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What is claimed is;

1. A semiconductor device comprising:
a semiconductor element;
an electrode pad formed at a primary surface of said semiconductor element;
a resin layer formed at said primary surface at which said electrode pad is formed;
a means for electrical connection that electrically connects said electrode pad to an external connection terminal; and
protective tape bonded onto a rear surface of said semiconductor element.
2. A semiconductor device according to claim 1, wherein:
said protective tape is constituted of a hardened synthetic resin achieving a bonding function.
3. A semiconductor device according to claim 1, wherein:
said means for electrical connection is constituted of a wiring and a conductive post.
4. A semiconductor device according to claim 1, wherein:
said external connection terminal is constituted of a solder ball.
5. A semiconductor device manufacturing method comprising:
a step in which a wafer having electrode pads formed at primary surfaces of semiconductor elements and means for electrical connection provided at said electrode pads is prepared;
a step in which protective tape is bonded onto a rear surface of said wafer;

a step in which said wafer is set at a die and said primary surface of said semiconductor element is sealed with a resin layer;

a step in which a front surface of said resin layer is polished;

a step in which external connection terminals are mounted to said means for electrical connection exposed at said front surface of said resin layer; and

a step in which said wafer having undergone the preceding steps is divided into individual pieces.

6. A semiconductor device manufacturing method according to claim 5, further comprising:

a step in which said protective tape is peeled off and said rear surface of said wafer is polished, that is implemented after said step in which said front surface of said resin layer is polished.

7. A semiconductor device manufacturing method according to claim 5, wherein:

said protective tape is peeled off through ultraviolet ray irradiation.

8. A semiconductor device manufacturing method according to claim 5, wherein:

said step in which said rear surface of said wafer is polished is implemented before a heat treatment.

9. A semiconductor device manufacturing method according to claim 5, wherein:

said protective tape is constituted of a hardened synthetic resin achieving a bonding function.

10. A semiconductor device manufacturing method according to claim 5, wherein:

said means for electrical connection is constituted of a wiring and conductive posts.

11. A semiconductor device manufacturing method according to claim 5, wherein:

said external connection terminals are constituted of solder balls.